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#7
7-3d-02

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :

PASCALE MOTTE ET AL

: ATTN: APPLICATION DIVISION

SERIAL NO: NEW PCT APPLICATION :
(Based on PCT/FR00/01891)

FILED: HEREWITH :

FOR: METHOD FOR DEPOSITING A
SILICON-CONTAINING
DIELECTRIC MATERIAL ON
COPPER

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Prior to examination on the merits, please amend the above-identified application as follows.

IN THE CLAIMS

Please cancel Claims 1-18.

Please add the following claims:

19. A method for depositing a dielectric material on copper apparent on the surface of a structure, entailing the following steps:

placing the structure in a deposit chamber of CVD type (Chemical Vapour

Deposition),

adding to the chamber a first gas forming a precursor for the formation of the dielectric material and containing an element able to contaminate copper,

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